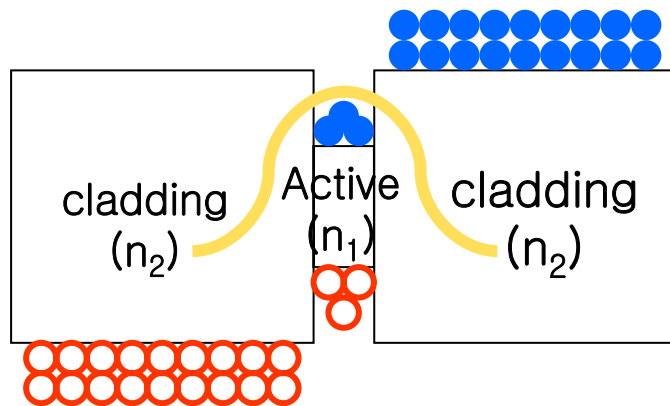


# Lect. 21: Single-Mode Semiconductor Laser

Two conditions for lasing: (1)  $\Gamma g_{\text{th}} = \alpha_{\text{m}} + \alpha_{\text{int}}$  and (2)  $\frac{\lambda}{n_{\text{eff}}} = \frac{2L}{m}$

There can be several lasing modes: several  $\lambda$ 's satisfying above conditions.

(1) Multi-mode waveguide



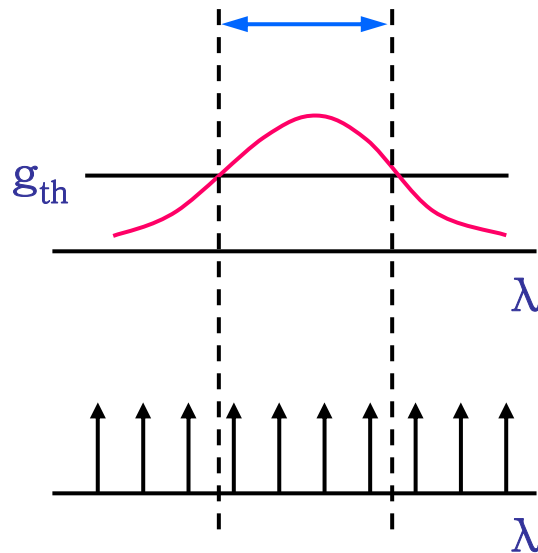
Different modes have different  $n_{\text{eff}}$ .

=> Design for single guided mode.

TE, TM modes?

# Lect. 21: Single-Mode Semiconductor Laser

Several cavity modes



$$\frac{\lambda}{n_{eff}} = \frac{2L}{m} \text{ for } g(\lambda) > g_{th}$$

Mode separation

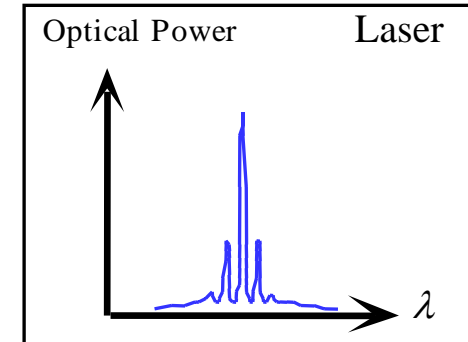
$$\text{From } e^{-j2nk_0L} = 1 \Rightarrow 2n_{eff}k_0L = 2m\pi$$

$$\Delta(n_{eff}k_0)L = \pi \Rightarrow \Delta(n_{eff}k_0) = \frac{\pi}{L}$$

$$\lambda = n_{eff} \frac{2\pi}{k_0} \therefore \Delta\lambda = \frac{\delta\lambda}{\delta k_0} \Delta k = -n_{eff} \frac{2\pi}{k_0^2} \Delta k = -\frac{\lambda^2}{2n_{eff}L}$$

With typical semiconductor lasers with cleaved facets,  $\Delta\lambda$  is less than gain bandwidth  $\Rightarrow$  multi lasing modes

$\rightarrow$  Fabry-Perot laser

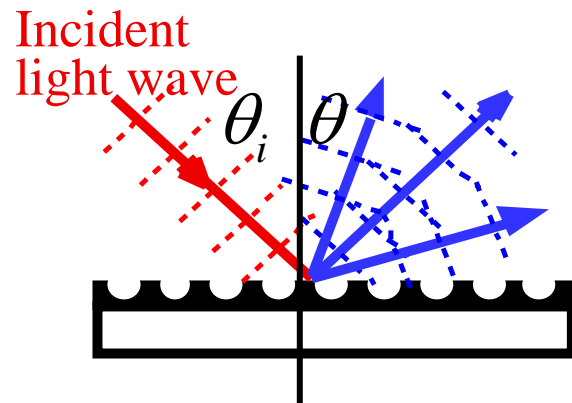


# Lect. 21: Single-Mode Semiconductor Laser

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Single-mode laser for long-distance, high-speed optical communications?

Use another type of mirror: Grating



$$d (\sin \theta - \sin \theta_i) = m \cdot \lambda$$

For  $\theta_i = 90^\circ$  and  $\theta = -90^\circ$ ,

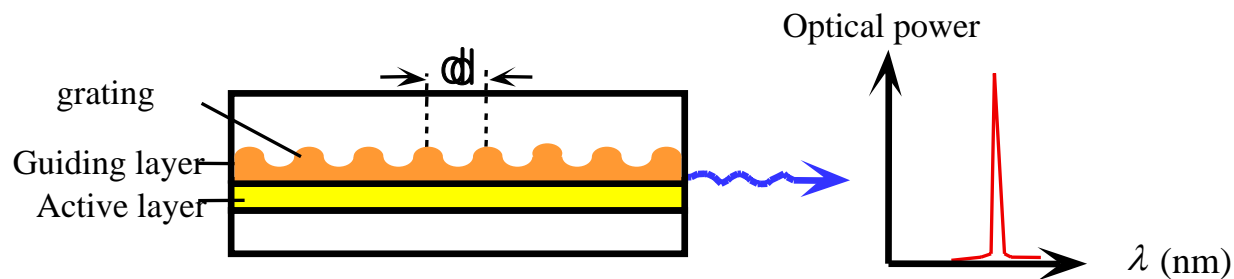
$$d = m \frac{\lambda}{2}$$

# Lect. 21: Single-Mode Semiconductor Laser

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How to implement diffraction grating within semiconductor laser?

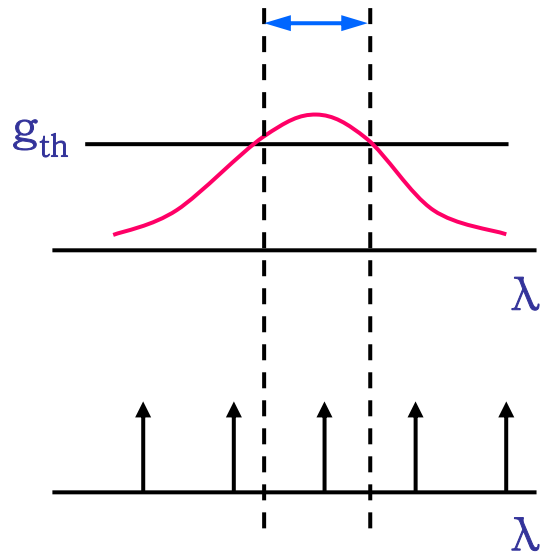
## Distributed Feedback (DFB) Laser



$$d = m \frac{\lambda}{2n_{\text{eff}}} \quad (\text{typically } m=1)$$

# Lect. 21: Single-Mode Semiconductor Laser

Another approach: Make  $L$  very small so that  $\Delta\lambda$  larger than gain bandwidth



gain bandwidth: in the order of 10nm

$\lambda$  :  $1.5\mu\text{m}$

$n_{eff}$  : 3.5

$L \sim 30\mu\text{m}$ ;

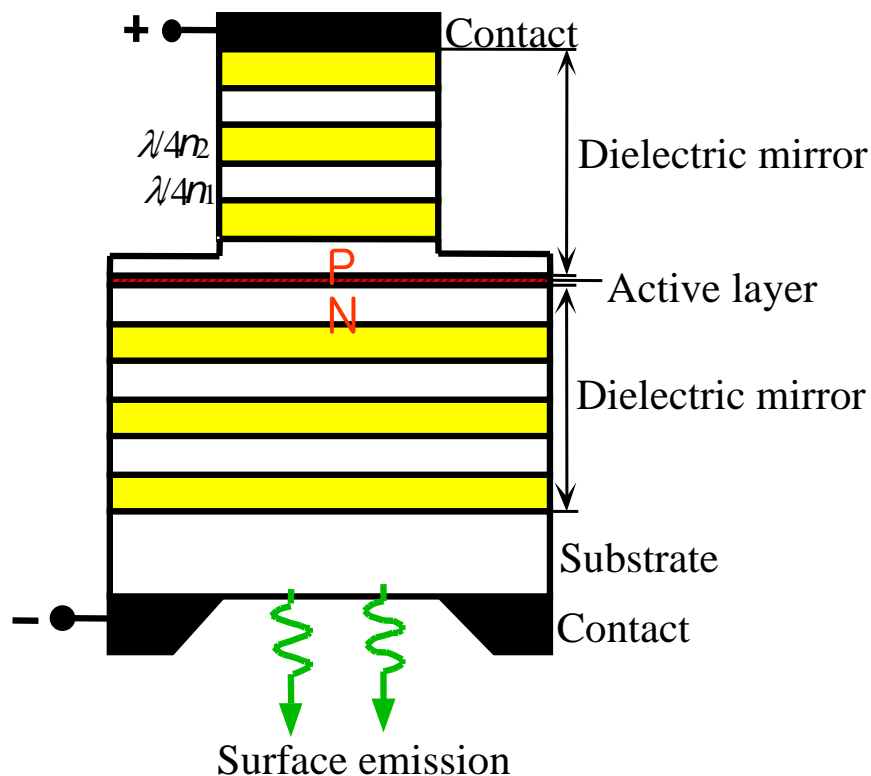
Not easy to fabricate by cleaving

$$|\Delta\lambda| = \frac{\lambda^2}{2n_{eff}L}$$

From  $\alpha_m = \frac{1}{L} \ln \frac{1}{R}$ , too much mirror loss

# Lect. 21: Single-Mode Semiconductor Laser

**Solution:** Very short cavity **vertical** lasers with very high reflectivity mirrors  
(**VCSEL**: Vertical Cavity Surface Emitting Laser)



In semiconductor fabrication, vertical thickness can be very precisely controlled.

Dielectric mirror can have high reflectivity approaching  $R=1$ .

$$\text{From } \alpha_m = \frac{1}{L} \ln \frac{1}{R},$$

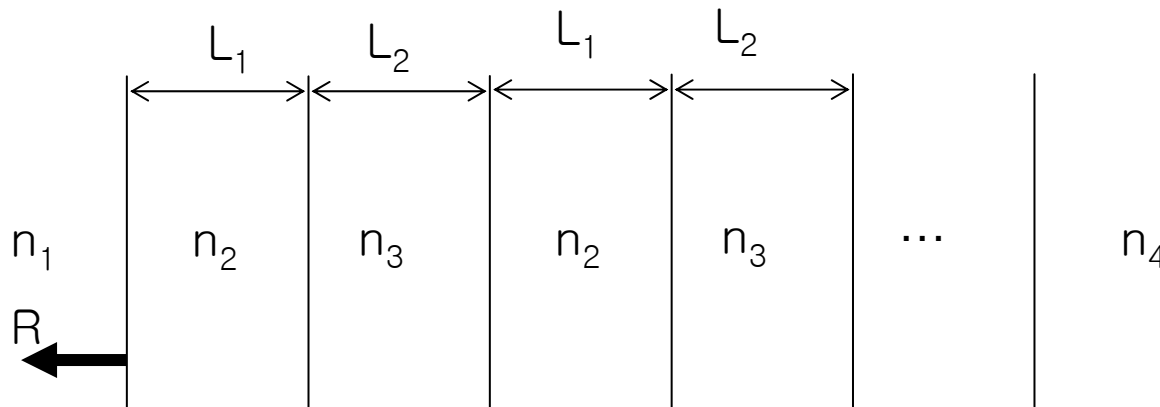
$\alpha_m$  can be made small if  $R$  approaches 1.

VCSELs are cheap because it is easy to make.

# Lect. 21: Single-Mode Semiconductor Laser

Review: High-Reflection Coating => Dielectric mirror

Repeat the quarter-wavelength pair m times.



$$R = \left( \frac{n_1 - \left(\frac{n_2}{n_3}\right)^{2m} n_4}{n_1 + \left(\frac{n_2}{n_3}\right)^{2m} n_4} \right)^2$$

If  $n_2 > n_3$ ,  $R \sim \left( \frac{-(n_2/n_3)^{2m} n_4}{+(n_2/n_3)^{2m} n_4} \right)^2 = 1$

If  $n_2 < n_3$ ,  $R \sim \left( \frac{n_1}{n_1} \right)^2 = 1$

# Lect. 21: Single-Mode Semiconductor Laser

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## Exercise Problems:

Prob. 9, Prob. 12, Prob. 15, Prob. 18, Prob. 20, Prob. 23 in Part 3

## Schedule for coming weeks:

- Nov. 21: Quiz 8, Lect. 22
  - Nov. 23: Lect. 23
  
  - Nov. 28: Quiz 9, Research Presentation (고민수, 윤순준)
  - Nov. 30: Research Presentation (이명재, 홍문기)
  - Dec. 5: Research Presentation (오택일)
- ➔ 25 minutes for each presentation



# Lect. 21: Single-Mode Semiconductor Laser

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## Special Topic Presentation

40 min. presentation on one of following topics:

- Nonlinear Optics in Fiber (이명재)
  - Silicon Raman Laser (홍문기)
  - Photonic Crystal (윤순준)
  - Slow Light (고민수)
  - Quantum Cascade Lasers (오택일)
- 
- Dec. 5: 고민수
  - Dec. 7: 윤순준
  - Dec. 12: 이명재, 홍문기
  - Dec. 14: 오택일

➔ Dinner together on Dec. 14